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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Det	ails
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Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	84MHz
Connectivity	I ² C, IrDA, LINbus, SDIO, SPI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, I ² S, POR, PWM, WDT
Number of I/O	81
Program Memory Size	384KB (384K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	96К х 8
Voltage - Supply (Vcc/Vdd)	1.7V ~ 3.6V
Data Converters	A/D 16x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f401vdt6

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

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2.1 Compatibility with STM32F4 series

The STM32F401xD/xE are fully software and feature compatible with the STM32F4 series (STM32F42x, STM32F43x, STM32F41x, STM32F405 and STM32F407)

The STM32F401xD/xE can be used as drop-in replacement of the other STM32F4 products but some slight changes have to be done on the PCB board.







3.9 Nested vectored interrupt controller (NVIC)

The devices embed a nested vectored interrupt controller able to manage 16 priority levels, and handle up to 62 maskable interrupt channels plus the 16 interrupt lines of the $Cortex^{\$}$ -M4 with FPU.

- Closely coupled NVIC gives low-latency interrupt processing
- Interrupt entry vector table address passed directly to the core
- Allows early processing of interrupts
- Processing of late arriving, higher-priority interrupts
- Support tail chaining
- Processor state automatically saved
- Interrupt entry restored on interrupt exit with no instruction overhead

This hardware block provides flexible interrupt management features with minimum interrupt latency.

3.10 External interrupt/event controller (EXTI)

The external interrupt/event controller consists of 21 edge-detector lines used to generate interrupt/event requests. Each line can be independently configured to select the trigger event (rising edge, falling edge, both) and can be masked independently. A pending register maintains the status of the interrupt requests. The EXTI can detect an external line with a pulse width shorter than the Internal APB2 clock period. Up to 81 GPIOs can be connected to the 16 external interrupt lines.

3.11 Clocks and startup

On reset the 16 MHz internal RC oscillator is selected as the default CPU clock. The 16 MHz internal RC oscillator is factory-trimmed to offer 1% accuracy at 25 °C. The application can then select as system clock either the RC oscillator or an external 4-26 MHz clock source. This clock can be monitored for failure. If a failure is detected, the system automatically switches back to the internal RC oscillator and a software interrupt is generated (if enabled). This clock source is input to a PLL thus allowing to increase the frequency up to 84 MHz. Similarly, full interrupt management of the PLL clock entry is available when necessary (for example if an indirectly used external oscillator fails).

Several prescalers allow the configuration of the two AHB buses, the high-speed APB (APB2) and the low-speed APB (APB1) domains. The maximum frequency of the two AHB buses is 84 MHz while the maximum frequency of the high-speed APB domains is 84 MHz. The maximum allowed frequency of the low-speed APB domain is 42 MHz.

The devices embed a dedicated PLL (PLLI2S) which allows to achieve audio class performance. In this case, the I²S master clock can generate all standard sampling frequencies from 8 kHz to 192 kHz.



3.14 Power supply supervisor

3.14.1 Internal reset ON

This feature is available for V_{DD} operating voltage range 1.8 V to 3.6 V.

The internal power supply supervisor is enabled by holding PDR_ON high.

The device has an integrated power-on reset (POR) / power-down reset (PDR) circuitry coupled with a Brownout reset (BOR) circuitry. At power-on, POR is always active, and ensures proper operation starting from 1.8 V. After the 1.8 V POR threshold level is reached, the option byte loading process starts, either to confirm or modify default thresholds, or to disable BOR permanently. Three BOR thresholds are available through option bytes.

The device remains in reset mode when V_{DD} is below a specified threshold, $V_{POR/PDR}$ or V_{BOR} , without the need for an external reset circuit.

The device also features an embedded programmable voltage detector (PVD) that monitors the V_{DD}/V_{DDA} power supply and compares it to the V_{PVD} threshold. An interrupt can be generated when V_{DD}/V_{DDA} drops below the V_{PVD} threshold and/or when V_{DD}/V_{DDA} is higher than the V_{PVD} threshold. The interrupt service routine can then generate a warning message and/or put the MCU into a safe state. The PVD is enabled by software.

3.14.2 Internal reset OFF

This feature is available only on packages featuring the PDR_ON pin. The internal power-on reset (POR) / power-down reset (PDR) circuitry is disabled by setting the PDR_ON pin to low.

An external power supply supervisor should monitor V_{DD} and should maintain the device in reset mode as long as V_{DD} is below a specified threshold. PDR_ON should be connected to this external power supply supervisor. Refer to *Figure 5: Power supply supervisor interconnection with internal reset OFF*.



Figure 5. Power supply supervisor interconnection with internal reset OFF⁽¹⁾

1. The PRD_ON pin is only available in the WLCSP49 and UFBGA100 packages.



There are three power modes configured by software when the regulator is ON:

- MR is used in the nominal regulation mode (With different voltage scaling in Run) In Main regulator mode (MR mode), different voltage scaling are provided to reach the best compromise between maximum frequency and dynamic power consumption.
- LPR is used in the Stop modes

The LP regulator mode is configured by software when entering Stop mode.

• Power-down is used in Standby mode.

The Power-down mode is activated only when entering in Standby mode. The regulator output is in high impedance and the kernel circuitry is powered down, inducing zero consumption. The contents of the registers and SRAM are lost.

Depending on the package, one or two external ceramic capacitors should be connected on the V_{CAP_1} and V_{CAP_2} pins. The V_{CAP_2} pin is only available for the LQFP100 and UFBGA100 packages.

All packages have the regulator ON feature.

3.15.2 Regulator OFF

The Regulator OFF is available only on the UFBGA100, which features the BYPASS_REG pin. The regulator is disabled by holding BYPASS_REG high. The regulator OFF mode allows to supply externally a V12 voltage source through V_{CAP-1} and V_{CAP-2} pins.

Since the internal voltage scaling is not managed internally, the external voltage value must be aligned with the targeted maximum frequency. Refer to *Table 14: General operating conditions*.

The two 2.2 μ F V_{CAP} ceramic capacitors should be replaced by two 100 nF decoupling capacitors. Refer to *Figure 18: Power supply scheme*.

When the regulator is OFF, there is no more internal monitoring on V12. An external power supply supervisor should be used to monitor the V12 of the logic power domain. PA0 pin should be used for this purpose, and act as power-on reset on V12 power domain.

In regulator OFF mode, the following features are no more supported:

- PA0 cannot be used as a GPIO pin since it allows to reset a part of the V12 logic power domain which is not reset by the NRST pin.
- As long as PA0 is kept low, the debug mode cannot be used under power-on reset. As a consequence, PA0 and NRST pins must be managed separately if the debug connection under reset or pre-reset is required.







The following conditions must be respected:

- V_{DD} should always be higher than V_{CAP_1} and V_{CAP_2} to avoid current injection between power domains.
- If the time for V_{CAP_1} and V_{CAP_2} to reach V₁₂ minimum value is faster than the time for V_{DD} to reach 1.7 V, then PA0 should be kept low to cover both conditions: until V_{CAP_1} and V_{CAP_2} reach V₁₂ minimum value and until V_{DD} reaches 1.7 V (see *Figure 8*).
- Otherwise, if the time for V_{CAP_1} and V_{CAP_2} to reach V_{12} minimum value is slower than the time for V_{DD} to reach 1.7 V, then PA0 could be asserted low externally (see *Figure 9*).
- If V_{CAP_1} and V_{CAP_2} go below V_{12} minimum value and V_{DD} is higher than 1.7 V, then a reset must be asserted on PA0 pin.
- Note: The minimum value of V₁₂ depends on the maximum frequency targeted in the application



The RTC and backup registers are supplied through a switch that is powered either from the V_{DD} supply when present or from the V_{BAT} pin.

3.17 Low-power modes

The devices support three low-power modes to achieve the best compromise between low power consumption, short startup time and available wakeup sources:

Sleep mode

In Sleep mode, only the CPU is stopped. All peripherals continue to operate and can wake up the CPU when an interrupt/event occurs.

• Stop mode

The Stop mode achieves the lowest power consumption while retaining the contents of SRAM and registers. All clocks in the 1.2 V domain are stopped, the PLL, the HSI RC and the HSE crystal oscillators are disabled. The voltage regulator can also be put either in normal or in low-power mode.

The device can be woken up from the Stop mode by any of the EXTI line (the EXTI line source can be one of the 16 external lines, the PVD output, the RTC alarm/ wakeup/ tamper/ time stamp events).

Standby mode

The Standby mode is used to achieve the lowest power consumption. The internal voltage regulator is switched off so that the entire 1.2 V domain is powered off. The PLL, the HSI RC and the HSE crystal oscillators are also switched off. After entering Standby mode, the SRAM and register contents are lost except for registers in the backup domain when selected.

The device exits the Standby mode when an external reset (NRST pin), an IWDG reset, a rising edge on the WKUP pin, or an RTC alarm/ wakeup/ tamper/time stamp event occurs.

Standby mode is not supported when the embedded voltage regulator is bypassed and the 1.2 V domain is controlled by an external power.

3.18 V_{BAT} operation

The VBAT pin allows to power the device V_{BAT} domain from an external battery, an external super-capacitor, or from V_{DD} when no external battery and an external super-capacitor are present.

 V_{BAT} operation is activated when V_{DD} is not present.

The VBAT pin supplies the RTC and the backup registers.

Note: When the microcontroller is supplied from VBAT, external interrupts and RTC alarm/events do not exit it from V_{BAT} operation. When PDR_ON pin is not connected to V_{DD} (internal Reset OFF), the V_{BAT} functionality is no more available and VBAT pin should be connected to V_{DD} .



4 Pinouts and pin description



1. The above figure shows the package bump side.





Figure 12. STM32F401xD/xE LQFP64 pinout

1. The above figure shows the package top view.



Bus	Boundary address	Peripheral
	0xE010 0000 - 0xFFFF FFFF	Reserved
Cortex [®] -M4	0xE000 0000 - 0xE00F FFFF	Cortex-M4 internal peripherals
	0x5004 0000 - 0xDFFF FFFF	Reserved
AHB2	0x5000 0000 - 0x5003 FFFF	USB OTG FS
	0x4002 6800 - 0x4FFF FFFF	Reserved
	0x4002 6400 - 0x4002 67FF	DMA2
	0x4002 6000 - 0x4002 63FF	DMA1
	0x4002 5000 - 0x4002 4FFF	Reserved
	0x4002 3C00 - 0x4002 3FFF	Flash interface register
	0x4002 3800 - 0x4002 3BFF	RCC
	0x4002 3400 - 0x4002 37FF	Reserved
	0x4002 3000 - 0x4002 33FF	CRC
ALIDI	0x4002 2000 - 0x4002 2FFF	Reserved
	0x4002 1C00 - 0x4002 1FFF	GPIOH
	0x4002 1400 - 0x4002 1BFF	Reserved
	0x4002 1000 - 0x4002 13FF	GPIOE
	0x4002 0C00 - 0x4002 0FFF	GPIOD
	0x4002 0800 - 0x4002 0BFF	GPIOC
	0x4002 0400 - 0x4002 07FF	GPIOB
	0x4002 0000 - 0x4002 03FF	GPIOA

Table 10. STM32F401xD register boundary addresses



Bus	Boundary address	Peripheral
	0x4001 4C00- 0x4001 FFFF	Reserved
	0x4001 4800 - 0x4001 4BFF	TIM11
	0x4001 4400 - 0x4001 47FF	TIM10
	0x4001 4000 - 0x4001 43FF	TIM9
	0x4001 3C00 - 0x4001 3FFF	EXTI
	0x4001 3800 - 0x4001 3BFF	SYSCFG
	0x4001 3400 - 0x4001 37FF	SPI4/I2S4
	0x4001 3000 - 0x4001 33FF	SPI1
	0x4001 2C00 - 0x4001 2FFF	SDIO
AFBZ	0x4001 2400 - 0x4001 2BFF	Reserved
	0x4001 2000 - 0x4001 23FF	ADC1
	0x4001 1800 - 0x4001 1FFF	Reserved
	0x4001 1400 - 0x4001 17FF	USART6
	0x4001 1000 - 0x4001 13FF	USART1
	0x4001 0800 - 0x4001 0FFF	Reserved
	0x4001 0400 - 0x4001 07FF	TIM8
	0x4001 0000 - 0x4001 03FF	TIM1
	0x4000 7400 - 0x4000 FFFF	Reserved



series combination of C_{L1} and C_{L2} . PCB and MCU pin capacitance must be included (10 pF can be used as a rough estimate of the combined pin and board capacitance) when sizing C_{L1} and C_{L2} .

Note:

For information on selecting the crystal, refer to the application note AN2867 "Oscillator design guide for ST microcontrollers" available from the ST website www.st.com.





1. R_{EXT} value depends on the crystal characteristics.

Low-speed external clock generated from a crystal/ceramic resonator

The low-speed external (LSE) clock can be supplied with a 32.768 kHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on characterization results obtained with typical external components specified in *Table 38*. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _F	Feedback resistor		-	18.4	-	MΩ
I _{DD}	LSE current consumption		-	-	1	μA
G _m _crit_max	Maximum critical crystal g _m	Startup	-	-	0.56	µA/V
t _{SU(LSE)} ⁽²⁾	startup time	V_{DD} is stabilized	-	2	-	S

Table 38. LSE oscillator characteristics (f_{LSE} = 32.768 kHz) ⁽¹⁾

1. Guaranteed by design, not tested in production.

 t_{SU(LSE)} is the startup time measured from the moment it is enabled (by software) to a stabilized 32.768 kHz oscillation is reached. This value is guaranteed by characterization and not tested in production. It is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer.

Note:

For information on selecting the crystal, refer to the application note AN2867 "Oscillator design guide for ST microcontrollers" available from the ST website www.st.com.





Figure 26. ACC_{HSI} versus temperature

1. Guaranteed by characterization, not tested in production.

Low-speed internal (LSI) RC oscillator

Table 4	40. LSI	oscillator	characteristics	(1)

Symbol	Parameter	Min	Тур	Мах	Unit
f _{LSI} ⁽²⁾	Frequency	17	32	47	kHz
t _{su(LSI)} ⁽³⁾	LSI oscillator startup time	-	15	40	μs
I _{DD(LSI)} ⁽³⁾	LSI oscillator power consumption	-	0.4	0.6	μA

1. V_{DD} = 3 V, T_A = -40 to 105 °C unless otherwise specified.

2. Guaranteed by characterization, not tested in production.

3. Guaranteed by design, not tested in production.



	Symbol	Ratings	Conditions	Class	Maximum value ⁽¹⁾	Unit
I	V _{ESD(HBM)}	Electrostatic discharge voltage (human body model)	$T_A = +25$ °C conforming to JESD22- A114	2	2000	
	V _{ESD(CDM)}	Electrostatic discharge voltage (charge device model)	T _A = +25 °C conforming to ANSI/ESD STM5.3.1	II	400	V

 Table 51. ESD absolute maximum ratings

1. Guaranteed by characterization, not tested in production.

Static latchup

Two complementary static tests are required on six parts to assess the latchup performance:

- A supply overvoltage is applied to each power supply pin
- A current injection is applied to each input, output and configurable I/O pin

These tests are compliant with EIA/JESD 78A IC latchup standard.

Table 52. Electrical sensitivities

Symbol	Parameter	Conditions	Class
LU	Static latch-up class	$T_A = +105 \text{ °C conforming to JESD78A}$	II level A

6.3.15 I/O current injection characteristics

As a general rule, current injection to the I/O pins, due to external voltage below V_{SS} or above V_{DD} (for standard, 3 V-capable I/O pins) should be avoided during normal product operation. However, in order to give an indication of the robustness of the microcontroller in cases when abnormal injection accidentally happens, susceptibility tests are performed on a sample basis during device characterization.

Functional susceptibilty to I/O current injection

While a simple application is executed on the device, the device is stressed by injecting current into the I/O pins programmed in floating input mode. While current is injected into the I/O pin, one at a time, the device is checked for functional failures.

The failure is indicated by an out of range parameter: ADC error above a certain limit (>5 LSB TUE), out of conventional limits of induced leakage current on adjacent pins (out of -5μ A/+0 μ A range), or other functional failure (for example reset, oscillator frequency deviation).

Negative induced leakage current is caused by negative injection and positive induced leakage current by positive injection.

The test results are given in *Table 53*.





Figure 37. I²S slave timing diagram (Philips protocol)⁽¹⁾

LSB transmit/receive of the previously transmitted byte. No LSB transmit/receive is sent before the first byte. 1.



Figure 38. I²S master timing diagram (Philips protocol)⁽¹⁾

LSB transmit/receive of the previously transmitted byte. No LSB transmit/receive is sent before the first 1. byte.

General PCB design guidelines

Power supply decoupling should be performed as shown in *Figure 42* or *Figure 43*, depending on whether V_{REF+} is connected to V_{DDA} or not. The 10 nF capacitors should be ceramic (good quality). They should be placed them as close as possible to the chip.





1. V_{REF+} and V_{REF-} inputs are both available on UFBGA100. V_{REF+} is also available on LQFP100. When V_{REF+} and V_{REF-} are not available, they are internally connected to V_{DDA} and V_{SSA} .





1. V_{REF+} and V_{REF-} inputs are both available on UFBGA100. V_{REF+} is also available on LQFP100. When V_{REF+} and V_{REF-} are not available, they are internally connected to V_{DDA} and V_{SSA} .



······································				
Dimension	Recommended values			
Pitch	0.4 mm			
Dpad	260 μm max. (circular) 220 μm recommended			
Dsm	300 μm min. (for 260 μm diameter pad)			
PCB pad design	Non-solder mask defined via underbump allowed			

Table 80. V	WLCSP49 r	recommended	PCB d	esian I	rules (0.4 mm	pitch)
14.510 001						•••••	p

Device marking



 Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.



7.1.2 UFQFPN48, 7 x 7 mm, 0.5 mm pitch package



Figure 49. UFQFPN48, 7 x 7 mm, 0.5 mm pitch, package outline

1. Drawing is not to scale.

- 2. All leads/pads should also be soldered to the PCB to improve the lead/pad solder joint life.
- 3. There is an exposed die pad on the underside of the UFQFPN package. It is recommended to connect and solder this back-side pad to PCB ground.

Symbol	millimeters			inches ⁽¹⁾			
	Min.	Тур.	Max.	Min.	Тур.	Max.	
А	0.500	0.550	0.600	0.0197	0.0217	0.0236	
A1	0.000	0.020	0.050	0.0000	0.0008	0.0020	
D	6.900	7.000	7.100	0.2717	0.2756	0.2795	
E	6.900	7.000	7.100	0.2717	0.2756	0.2795	
D2	5.500	5.600	5.700	0.2165	0.2205	0.2244	
E2	5.500	5.600	5.700	0.2165	0.2205	0.2244	
L	0.300	0.400	0.500	0.0118	0.0157	0.0197	

Table 81. UFQFPN48, 7 x 7 mm, 0.5 mm pitch, package mechanical data



7.2 Thermal characteristics

The maximum chip junction temperature (T_Jmax) must never exceed the values given in *Table 14: General operating conditions on page 60.*

The maximum chip-junction temperature, T_J max., in degrees Celsius, may be calculated using the following equation:

 $T_J max = T_A max + (PD max x \Theta_{JA})$

Where:

- T_A max is the maximum ambient temperature in °C,
- Θ_{JA} is the package junction-to-ambient thermal resistance, in °C/W,
- PD max is the sum of P_{INT} max and P_{I/O} max (PD max = P_{INT} max + P_{I/O}max),
- P_{INT} max is the product of I_{DD} and V_{DD}, expressed in Watts. This is the maximum chip internal power.

 $P_{I/O}$ max represents the maximum power dissipation on output pins where:

 $\mathsf{P}_{\mathsf{I}/\mathsf{O}} \max = \Sigma \left(\mathsf{V}_{\mathsf{OL}} \times \mathsf{I}_{\mathsf{OL}}\right) + \Sigma((\mathsf{V}_{\mathsf{DD}} - \mathsf{V}_{\mathsf{OH}}) \times \mathsf{I}_{\mathsf{OH}}),$

taking into account the actual V_{OL} / I_{OL} and V_{OH} / I_{OH} of the I/Os at low and high level in the application.

Symbol	Parameter	Value	Unit
Θ _{JA}	Thermal resistance junction-ambient UFQFPN48	32	
	Thermal resistance junction-ambient WLCSP49	51	
	Thermal resistance junction-ambient LQFP64	50	°C/W
	Thermal resistance junction-ambient LQFP100	42	
	Thermal resistance junction-ambient UFBGA100	56	

Table 85. Package thermal characteristics

7.2.1 Reference document

JESD51-2 Integrated Circuits Thermal Test Method Environment Conditions - Natural Convection (Still Air). Available from www.jedec.org.

